SPD15N65T1

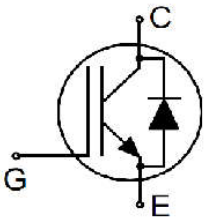
650V /15A Trench Field Stop IGBT

Features

- Max Junction Temperature 150°C
- High breakdown voltage up to 650V for improved reliability
- Short Circuit Rated
- Very Low Saturation Voltage:

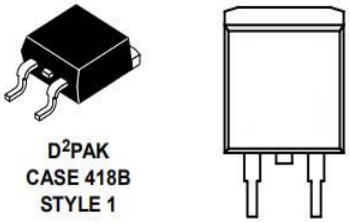
  $V_{CE(SAT)}$ = 1.65V (Typ.) @ I_C = 15A
- Soft current turn-off waveforms

V_{CE}	**650**	**V**
I_C	**15**	**A**
$V_{CE(SAT)}$ I_C=15A	**1.65**	**V**



Applications

- Soft switching applications
- Air conditioning
- Motor drive inverter



Product	Package	Packaging
SPD15N65T1	TO-263	Tube

Maximum Ratings （T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC collector current, limited by T_{jmax} T_C = 25°C T_C = 100°C	I_C	 30 15	A
Diode Forward current, limited by T_{jmax} T_C = 25°C T_C = 100°C	I_F	 30 15	A
Continuous Gate-emitter voltage	V_{GE}	±20	V
Transient Gate-emitter voltage	V_{GE}	±30	V
Turn off safe operating area V_{CE} ≤650V, T_j≤ 150°C	-	60	A
Pulsed collector current, V_{GE}=15V, t_p limited by T_{jmax}	I_{CM}	45	A
Short Circuit Withstand Time, V_{GE}= 15V, V_{CE}≤ 400V	T_{sc}	5	μs
Power dissipation , T_j=25℃	Ptot	27	W
Operating junction temperature	T_j	-40...+150	°C
Storage temperature	Ts	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	-	260	°C

Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT thermal resistance, junction - case	R_{θ}(j-c)	4.9	K/W
Diode thermal resistance, junction - case	R_{θ}(j-c)	5.8	K/W
Thermal resistance, junction - ambient	R_{θ}(j-a)	62.5	K/W

Electrical Characteristics of the IGBT（T_j= 25℃ unless otherwise specified）

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Static Characteristics (Tested on wafers)						
BV_{CES}	Collector to Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 1mA	650	-	-	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	I_C = 15A, V_{GE} = 15V	-	1.65	1.95	V
$V_{GE(th)}$	G-E Threshold Voltage	V_{GE} = V_{CE}, I_C = 250μA	4.1	5.0	5.7	V
I_{CES}	Collector Cut-Off Current	V_{CE} = 650V, V_{GE} = 0V	-	-	10	μA
I_{GES}	G-E Leakage Current	V_{GE} = ±20V, V_{CE} = 0V	-	-	±200	nA
g_{fs}	Transconductance	V_{CE}=20V, I_C=15A	-	10	-	S

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	1910	-	pF
Output capacitance	C_{oes}		-	80	-	
Reverse transfer capacitance	C_{res}		-	46	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 15A, V_{GE} = 15V	-	92	-	nC
Short circuit collector current	$I_{C(SC)}$	V_{GE}=15V,t_{SC}≤5us V_{CC}=400V, $T_{j,\ start}$=25°C	-	98	-	A

Switching Characteristic, Inductive Load（T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Turn-on Delay Time	$t_{d(on)}$	T_j=25°C V_{CC} = 400V, I_C = 15A, V_{GE} = 0/15V, Rg=12Ω	-	15	-	ns
Rise Time	t_r		-	25	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	60	-	ns
Fall Time	t_f		-	46	-	ns
Turn-on Energy	E_{on}		-	0.75	-	mJ
Turn-off Energy	E_{off}		-	0.1	-	mJ

Electrical Characteristics of the DIODE（T_j= 25℃ unless otherwise specified）

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Dynamic						
Diode Forward Voltage	V_{FM}	I_F = 15A	-	1.7	-	V
Reverse Recovery Time	*Trr*	I_F= 15A VR = 300V, di/dt =200A/μs	-	50	-	ns
Reverse Recovery Current	*Irr*		-	4	-	A
Reverse Recovery Charge	*Qrr*		-	83	-	nC

Fig. 1 FBSOA characteristics

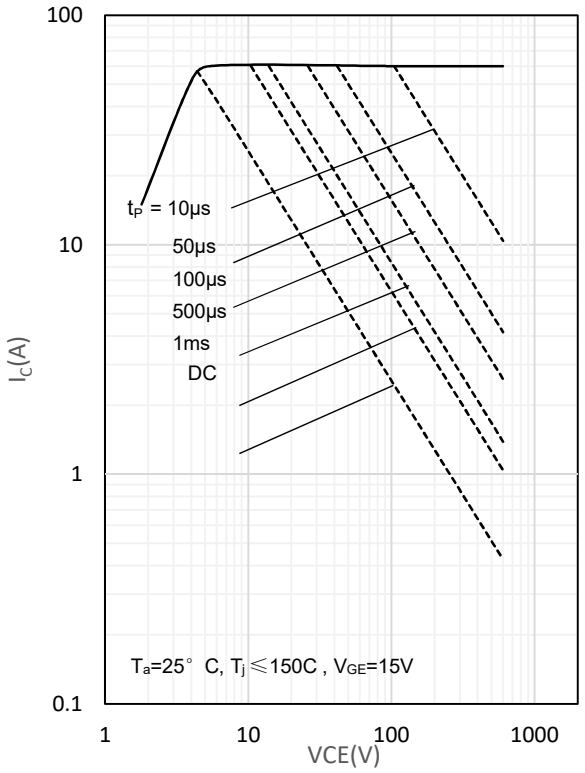


Fig. 2 Load Current vs. Frequency

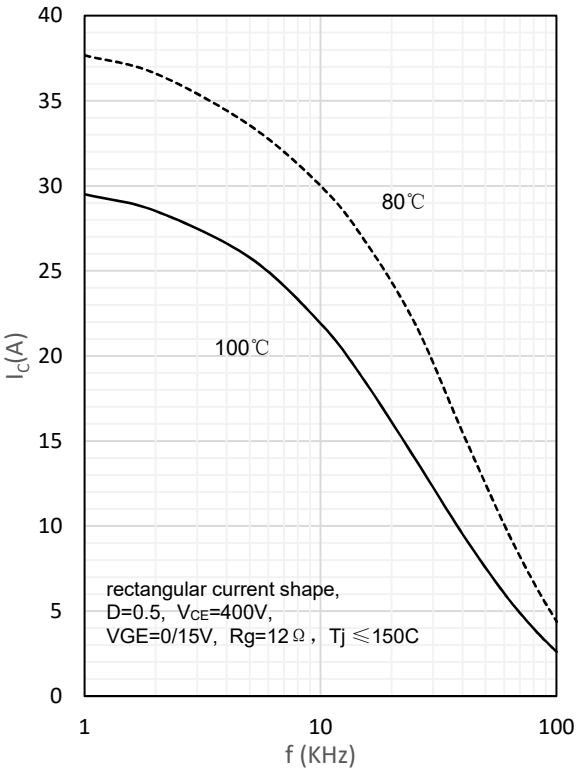


Fig. 3 Output characteristics

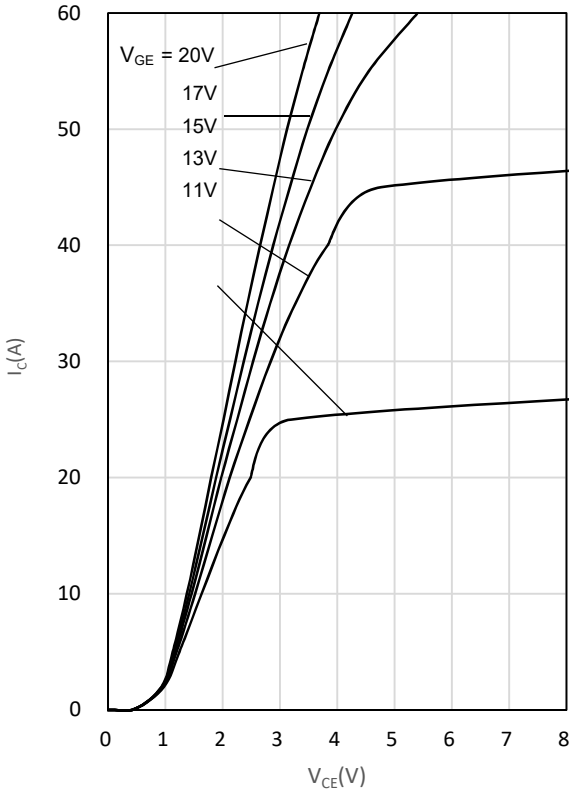


Fig. 4 Saturation voltage characteristics

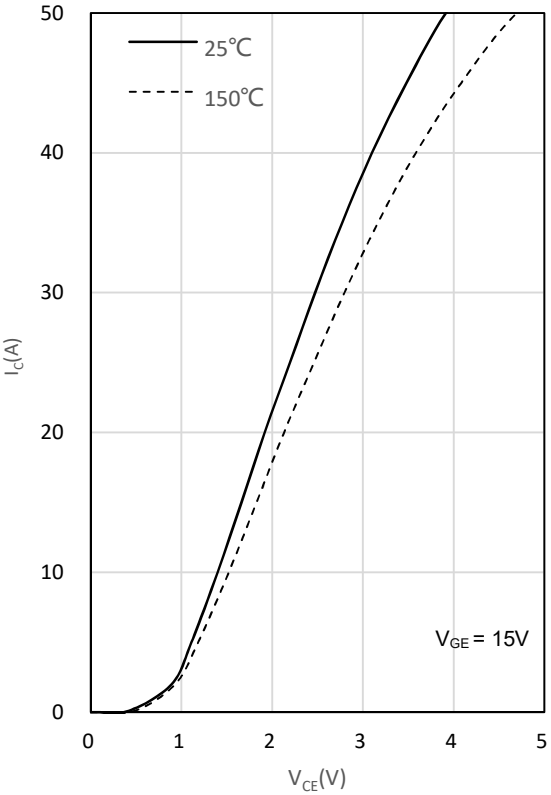


Fig. 5 Switching times vs. gate resistor

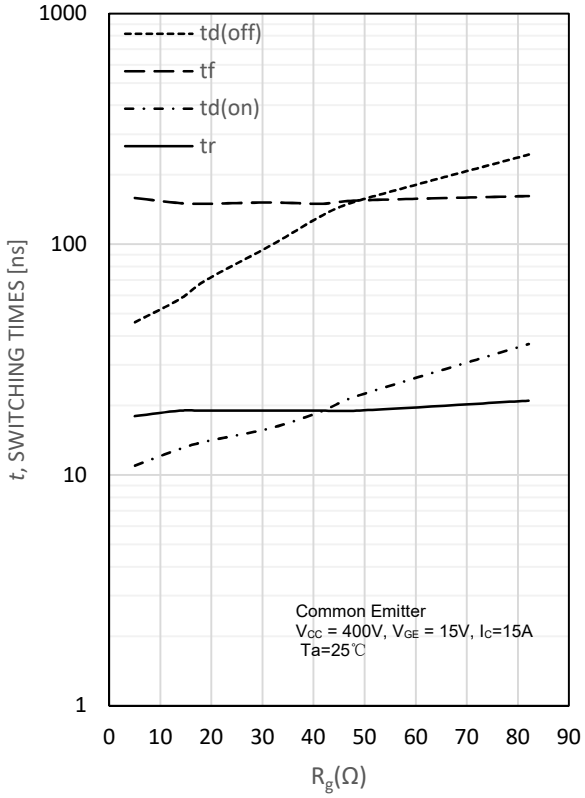


Fig. 6 Switching times vs. collector current

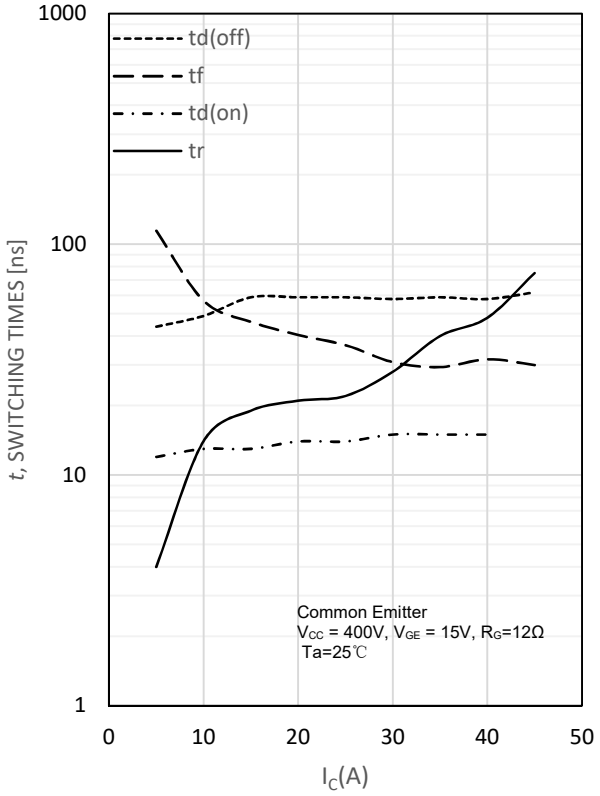


Fig. 7 Switching loss vs. gate resistor

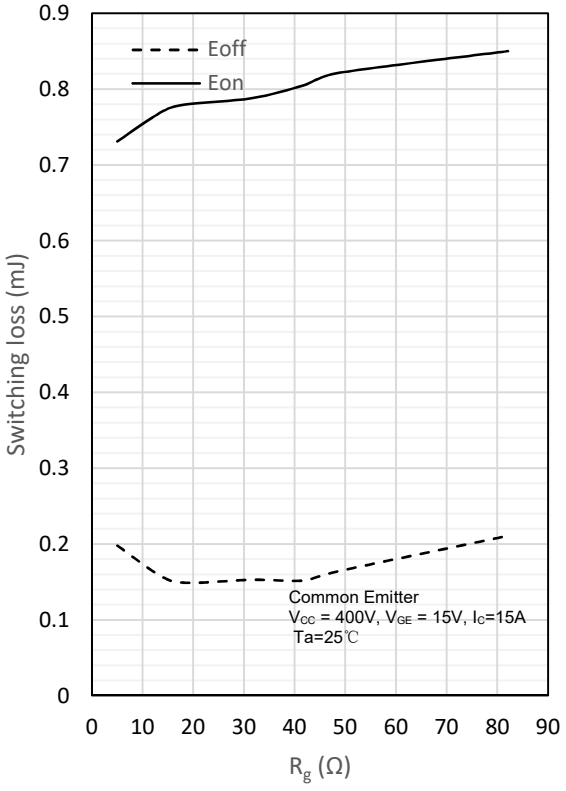


Fig. 8 Switching loss vs. collector current

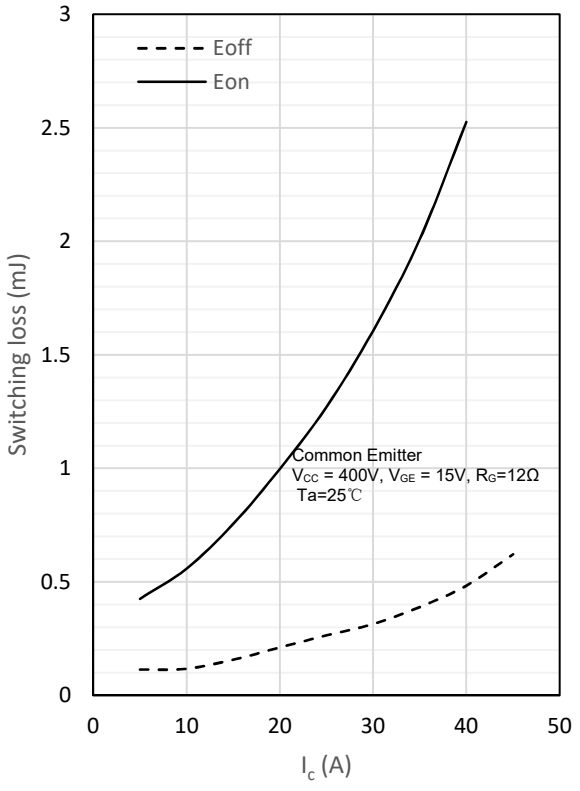


Fig. 9 Gate charge characteristics

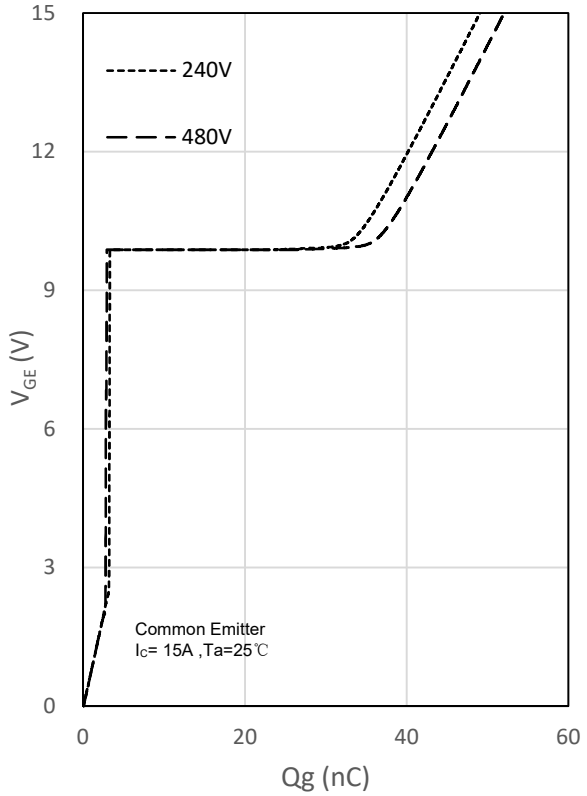


Fig. 10 Capacitance characteristics

